

Docket No. 501.43296X00  
Serial No. 10/733,377  
April 27, 2005

**AMENDMENTS TO THE SPECIFICATION:**

Please amend the Substitute Specification, submitted with the Preliminary Amendment filed January 8, 2004, in the above-identified application (hereinafter "Applicants' Substitute Specification), as follows:

Please delete the paragraph on page 1, lines 8-17, and substitute therefor the following new paragraph:

--As a silicide process for the purpose of suppressing spikes of Co silicide, there is a known technique of depositing a Co film and a TiN film (oxidation barrier film) on the surface of the source and drain of a silicon substrate, forming a dicobalt silicide ( $Co_2Si$ ) film by application of a first heat treatment at a temperature less than 400°C, removing the TiN film and an unreacted Co film by wet etching, and forming a cobalt disilicide ( $CoSi_2$ ) ( $Co_2Si$ ) film by application of a second heat treatment at a temperature ranging from 700 to 900°C (refer to Japanese Unexamined Patent Publication No. Hei 11(1999)-283935, U.S. Patent No. 6221764, Japanese Unexamined Patent Publication No. 2000-243726 and U.S. Patent No. 6337272).--

Please delete the paragraph on page 5, lines 1-4, and substitute therefor the following new paragraph:

-(d) after the step (c), heating the silicon wafer at a temperature of 400°C or greater, but less than 700°C, in the heat treatment chamber of the sputtering apparatus to convert the main component of the silicide layer from dicobalt silicide into cobalt monosilicide ( $CoSi$ ) ( $Co_2Si$ );--